

## Silicon PNP transistor epitaxial type AP020

### [ Applications ]

High voltage driver

### [ Feature ]

High voltage  $V_{CEO} = V_{CBO} = -300V$

### [ Absolute maximum ratings (Ta=25C) ]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	VCBO	-300	V
Collector-emitter voltage	VCEO	-300	V
Emitter-base voltage	VEBO	-7	V
Collector current	IC	-100	mA
Junction temperature	Tj	150	C
Storage temperature	Tstg	-55 to 150	C

### [ Electrical characteristics (Ta=25C) ]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BVCBO	-300	-	-	V	IC= -50uA, IE= 0A
Collector-emitter breakdown voltage	BVCEO	-300	-	-	V	IC= -10mA, IB= 0A
Emitter-base breakdown voltage	BVEBO	-7	-	-	V	IE= -50uA, IC= 0A
Collector-cut off current	ICBO	-	-	-500	nA	VCB= -300V, IE= 0A
DC current gain	hFE	60	-	280	-	VCE= -10V, IC= -10mA
Collector-emitter saturation voltage	VCE(sat)	-	-	-0.5	V	IC= -100mA, IB= -10mA
Transition frequency	fT	-	65	-	MHz	VCE= -10V, IE= 10mA
Collector output capacitance	Cob	-	4.5	-	pF	VCB= -20V, f= 1MHz, IE= 0A

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.